

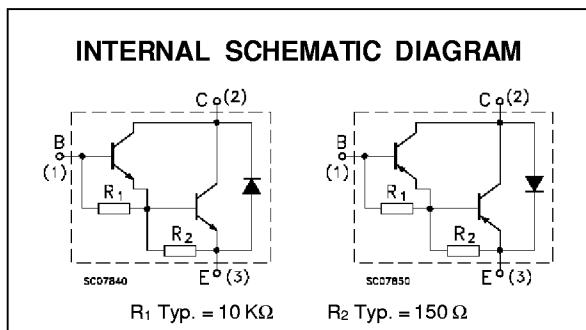
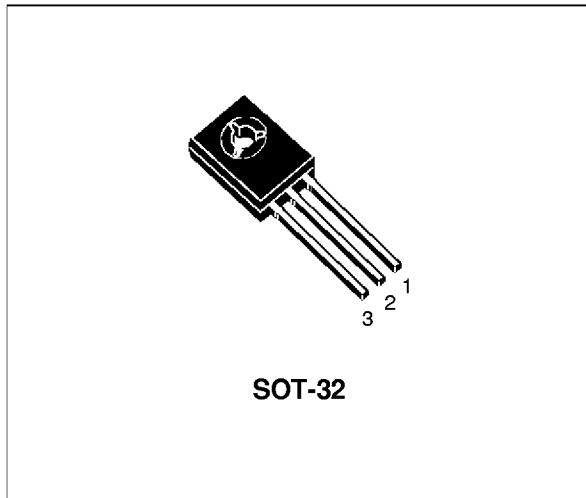
COMPLEMENTARY SILICON
 POWER DARLINGTON TRANSISTORS

- 2N6036 AND 2N6039 ARE SGS-THOMSON PREFERRED SALES TYPES

DESCRIPTION

The 2N6038 and 2N6039 are silicon epitaxial-base NPN power transistors in monolithic Darlington configuration mounted in Jedec SOT-32 plastic package.

The complementary PNP types are 2N6035 and 2N6036 respectively.


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		PNP	NPN	
V _{CBO}	Collector-Base Voltage ($I_E = 0$)	60	80	V
V _{CEO}	Collector-Emitter Voltage ($I_B = 0$)	60	80	V
V _{EBO}	Emitter-Base Voltage ($I_C = 0$)	5		V
I _C	Collector Current	4		A
I _{CM}	Collector Peak Current	8		A
I _B	Base Current	0.1		A
P _{tot}	Total Dissipation at $T_c \leq 25^\circ\text{C}$	40		W
T _{stg}	Storage Temperature	-65 to 150		°C
T _J	Max. Operating Junction Temperature	150		°C

For PNP types voltage and current values are negative.

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.12	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	83.3	°C/W

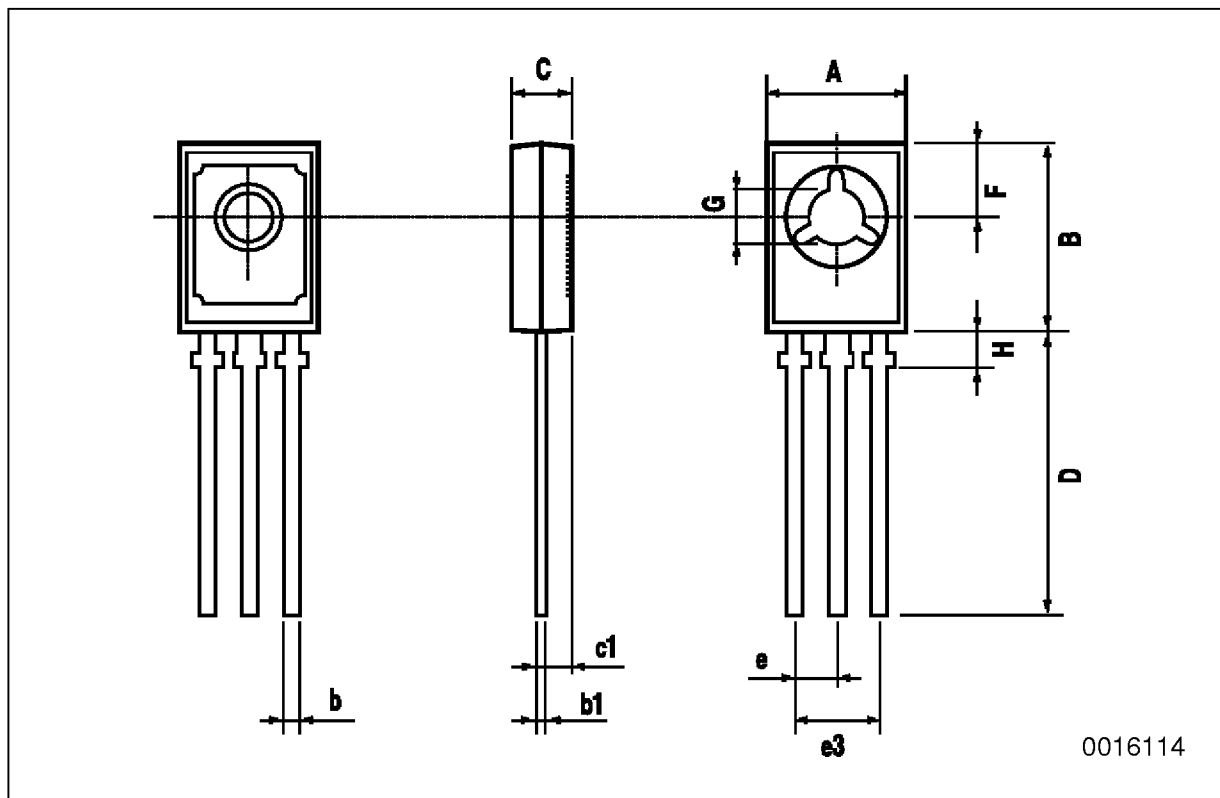
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEx}	Collector Cut-off Current ($V_{BE} = -1.5\text{V}$)	$V_{CE} = \text{rated } V_{CEO}$ $V_{CE} = \text{rated } V_{CEO} \quad T_c = 125^\circ\text{C}$			0.1 0.5	mA mA
I _{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CE} = \text{rated } V_{CBO}$			0.1	mA
I _{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = \text{rated } V_{CEO}$			0.1	mA
I _{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{V}$			2	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage	$I_C = 100\text{ mA}$ for 2N6035/2N6038 for 2N6036/2N6039	60 80			V V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	$I_C = 2\text{ A} \quad I_B = 8\text{ mA}$ $I_C = 4\text{ A} \quad I_B = 40\text{ mA}$			2 3	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	$I_C = 4\text{ A} \quad I_B = 40\text{ mA}$			4	V
V _{BE*}	Base-Emitter Voltage	$I_C = 2\text{ A} \quad V_{CE} = 3\text{ V}$			2.8	V
h_{FE}^*	DC Current Gain	$I_C = 0.5\text{ A} \quad V_{CE} = 3\text{ V}$ $I_C = 2\text{ A} \quad V_{CE} = 3\text{ V}$ $I_C = 4\text{ A} \quad V_{CE} = 3\text{ V}$	500 750 100		15000	
h_{fe}	Small Signal Current Gain	$I_C = 0.75\text{ A} \quad V_{CE} = 10\text{ V} \quad f = 1\text{KHz}$	25			
C _{CBO}	Collector Base Capacitance	$I_E = 0 \quad V_{CB} = 10\text{ V} \quad f = 1\text{MHz}$ for NPN types for PNP types			100 200	pF pF

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

SOT-32 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	7.4		7.8	0.291		0.307
B	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
C	2.4		2.7	0.04		0.106
c1		1.2			0.047	
D		15.7			0.618	
e		2.2			0.087	
e3		4.4			0.173	
F		3.8			0.150	
G	3		3.2	0.118		0.126
H			2.54			0.100



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